

## NCE P-Channel Enhancement Mode Power MOSFET

### Description

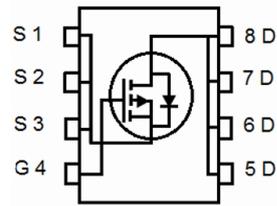
The NCE01P03S uses advanced trench technology and design to provide excellent  $R_{DS(on)}$  with low gate charge. It can be used in a wide variety of applications.

### General Features

- $V_{DS} = -100\text{ V}, I_D = -3\text{ A}$   
 $R_{DS(on)} < 200\text{ m}\Omega @ V_{GS} = -10\text{ V}$   
 $R_{DS(on)} < 230\text{ m}\Omega @ V_{GS} = -4.5\text{ V}$
- High density cell design for ultra low  $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- 100% Rg tested
- 100%  $\Delta V_{ds}$  tested
- 100% UIS tested

### Application

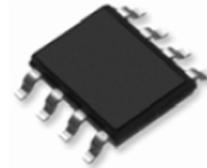
- Switching applications
- DC-DC converter



Schematic diagram



Marking and pin assignment



SOP-8L Top View

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE01P03S	NCE01P03S	SOP-8L	Ø330mm	12mm	5000units

### Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-3	A
Drain Current-Continuous( $T_A = 75^\circ\text{C}$ )	$I_D(75^\circ\text{C})$	-2.3	A
Pulsed Drain Current	$I_{DM}$	-12	A
Maximum Power Dissipation	$P_D$	3	W
De-rating factor		0.0244	W/ $^\circ\text{C}$
Single pulse avalanche energy <sup>(Note 1)</sup>	$E_{AS}$	49	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ\text{C}$

### Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	20	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient <sup>(Note 3)</sup>	$R_{\theta JA}$	41	$^\circ\text{C}/\text{W}$

## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

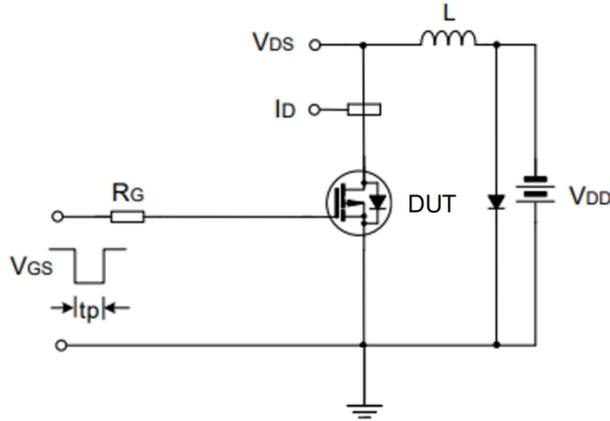
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-100	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-100V, V <sub>GS</sub> =0V	-	-	-1	uA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±10	uA
<b>On Characteristics</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1	-1.9	-3	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-2A	-	170	200	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A	-	200	230	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-3A	-	13	-	S
<b>Dynamic Characteristics</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-50V, V <sub>GS</sub> =0V, F=1.0MHz	-	1452	-	pF
Output Capacitance	C <sub>oss</sub>		-	48	-	pF
Reverse Transfer Capacitance	C <sub>riss</sub>		-	44	-	pF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-50V, I <sub>D</sub> =-3A, V <sub>GS</sub> =-10V, R <sub>GEN</sub> =3Ω	-	14	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	18	-	nS
Turn-off Delay Time	t <sub>d(off)</sub>		-	50	-	nS
Turn-off Fall Time	t <sub>f</sub>		-	18	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-50V, I <sub>D</sub> =-3A, V <sub>GS</sub> =-10V	-	29.9	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	3.8	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	7.4	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-2A	-	-	-1.2	V
Diode Forward Current	I <sub>S</sub>		-	-	-3	A

### Notes:

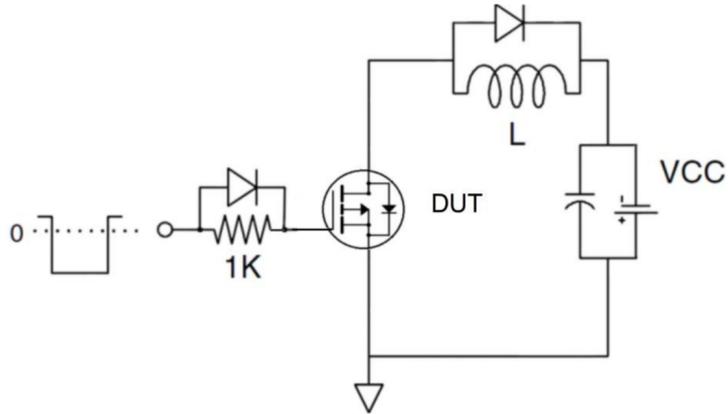
1. EAS condition : T<sub>j</sub>=25°C, V<sub>DD</sub>=-50V, V<sub>G</sub>=-10V, L=0.5mH, R<sub>g</sub>=25Ω.
2. The R<sub>θJC</sub> is the thermal impedance from junction to lead.
3. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub> =25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 150°C may be used if the PCB allows it.
4. Guaranteed by design, not subject to production.
5. These curves are based on the junction-to-ambient thermal impedance, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150°C. The SOA curve provides a single pulse rating.

**Test Circuit**

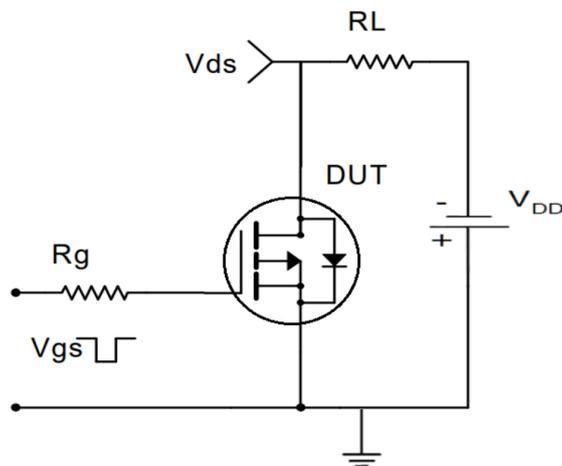
**1) E<sub>AS</sub> Test Circuit**



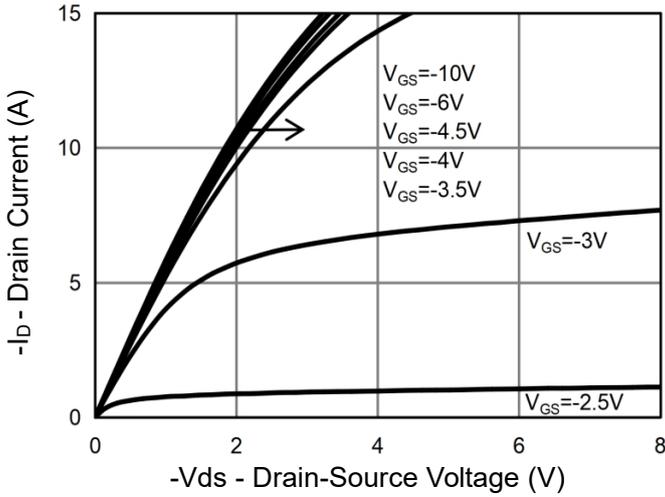
**2) Gate Charge Test Circuit**



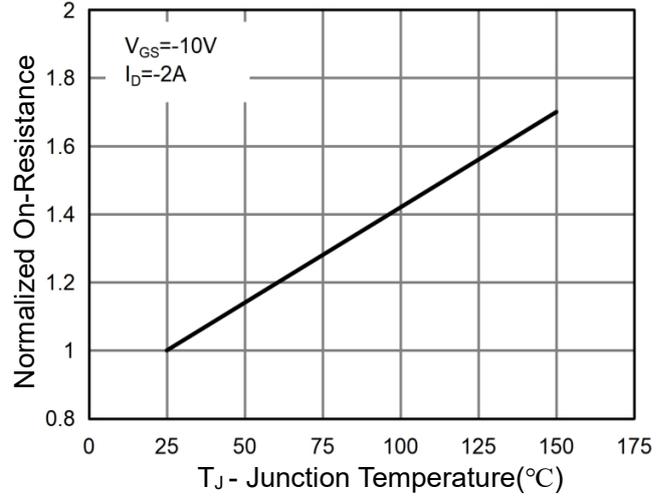
**3) Switch Time Test Circuit**



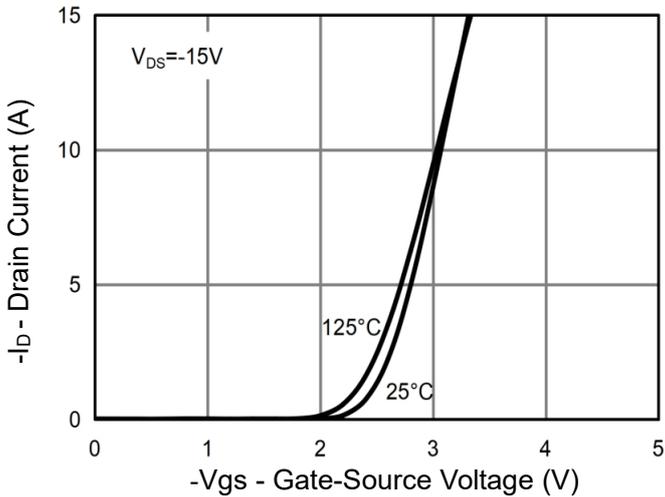
**Typical Electrical and Thermal Characteristics (Curves)**



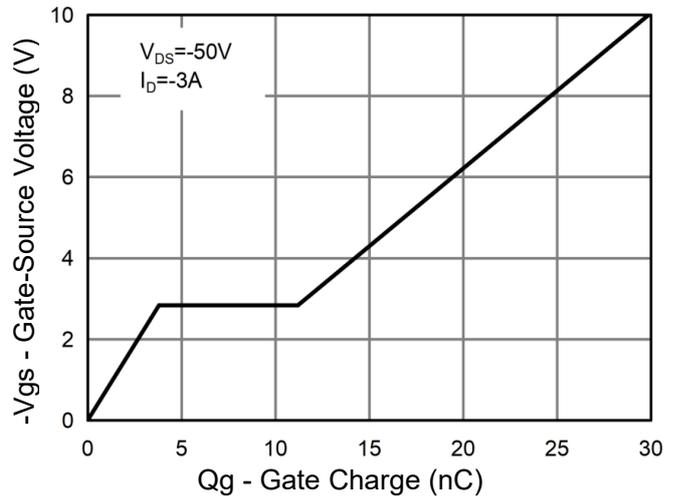
**Figure 1 Output Characteristics**



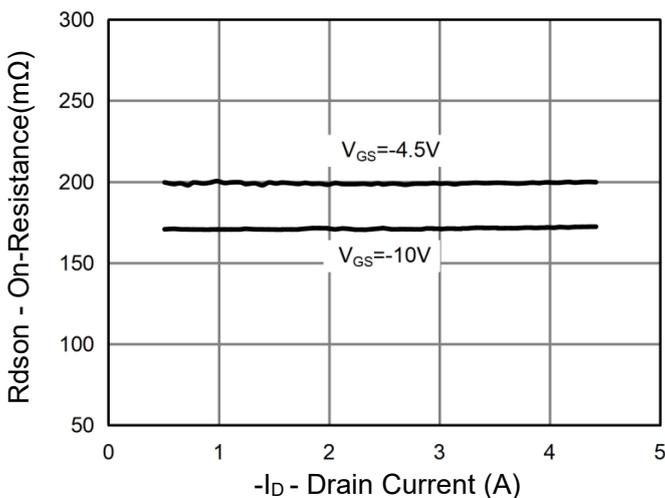
**Figure 4 Rds(on) vs Junction Temperature**



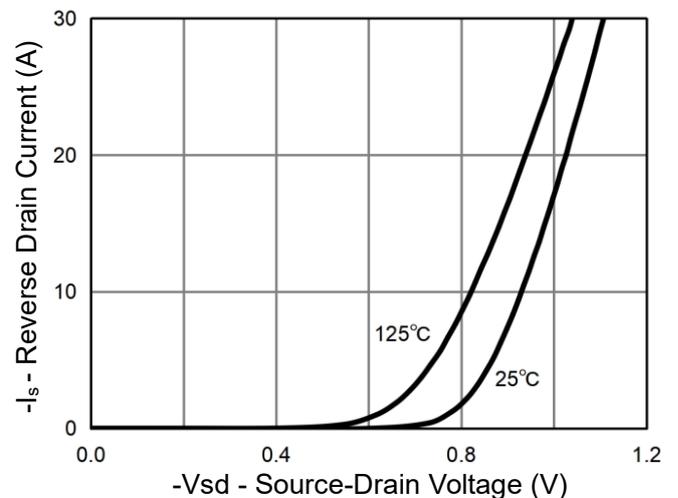
**Figure 2 Transfer Characteristics**



**Figure 5 Gate Charge**



**Figure 3 Rds(on) vs Drain Current**



**Figure 6 Source-Drain Diode Forward**

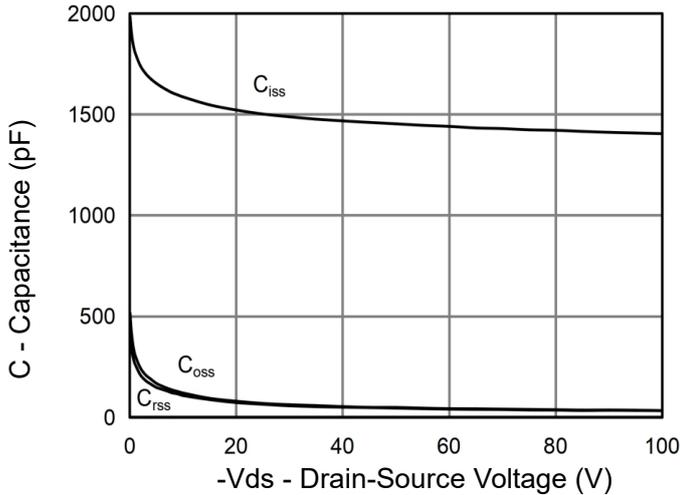


Figure 7 Capacitance vs Vds

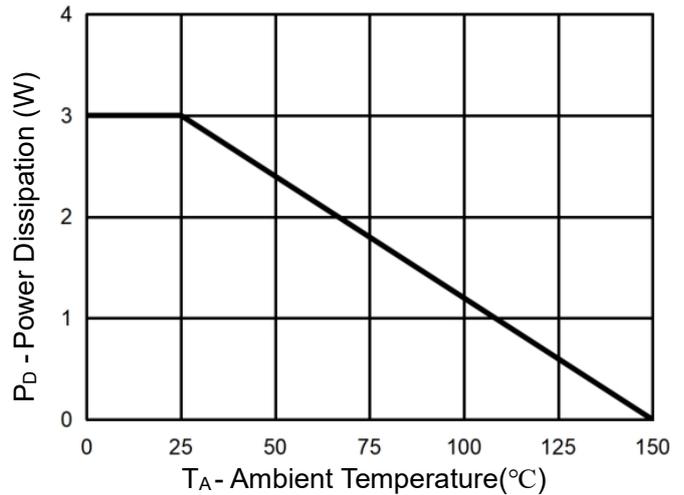


Figure 9 Power De-rating

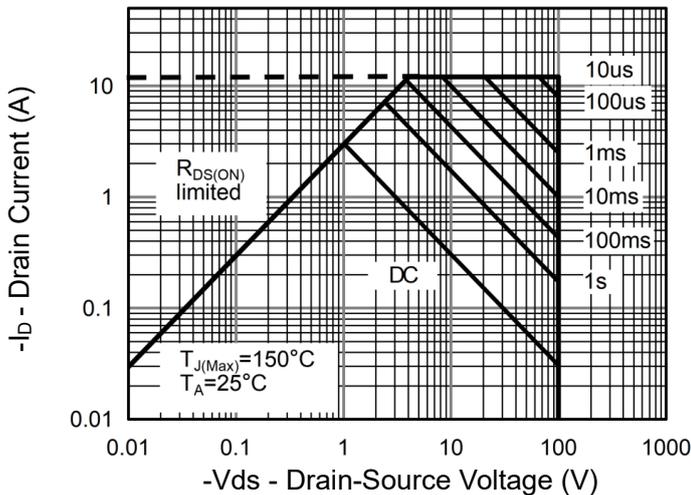


Figure 8 Safe Operation Area (Note 5)

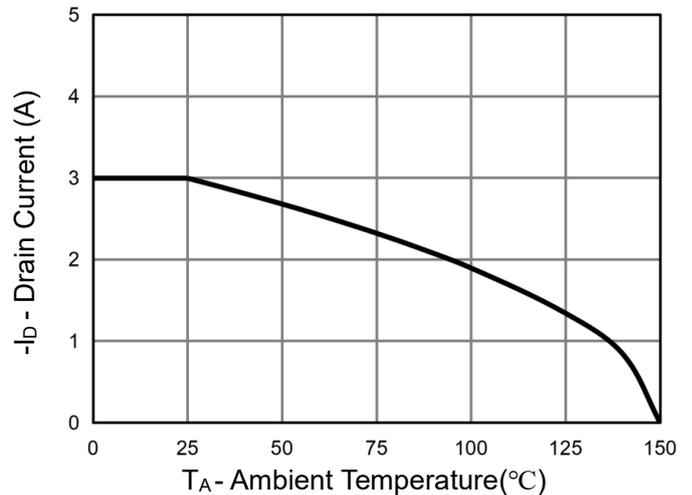


Figure 10 Drain Current De-rating

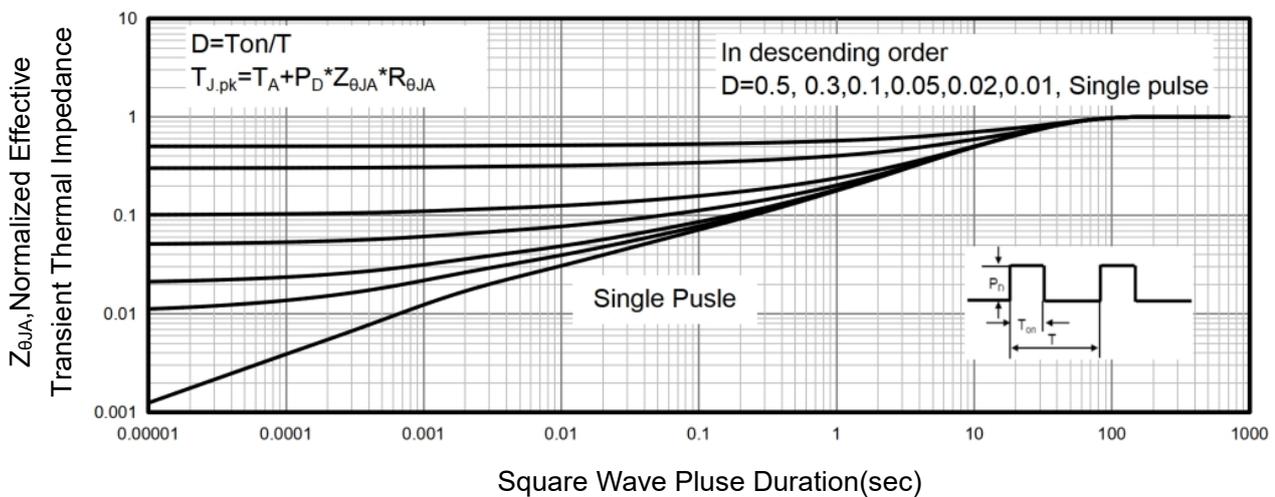
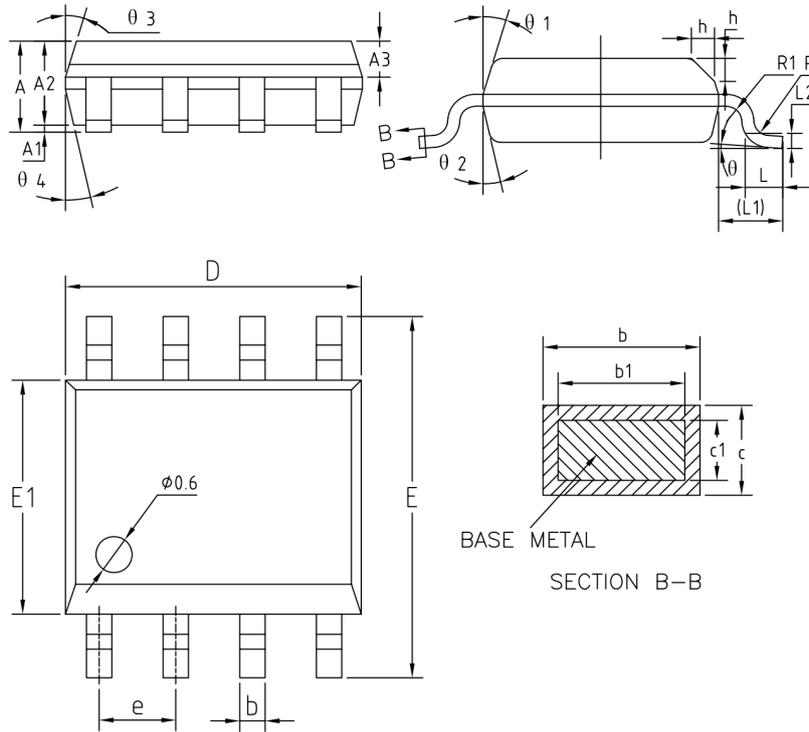


Figure 11 Normalized Maximum Transient Thermal Impedance

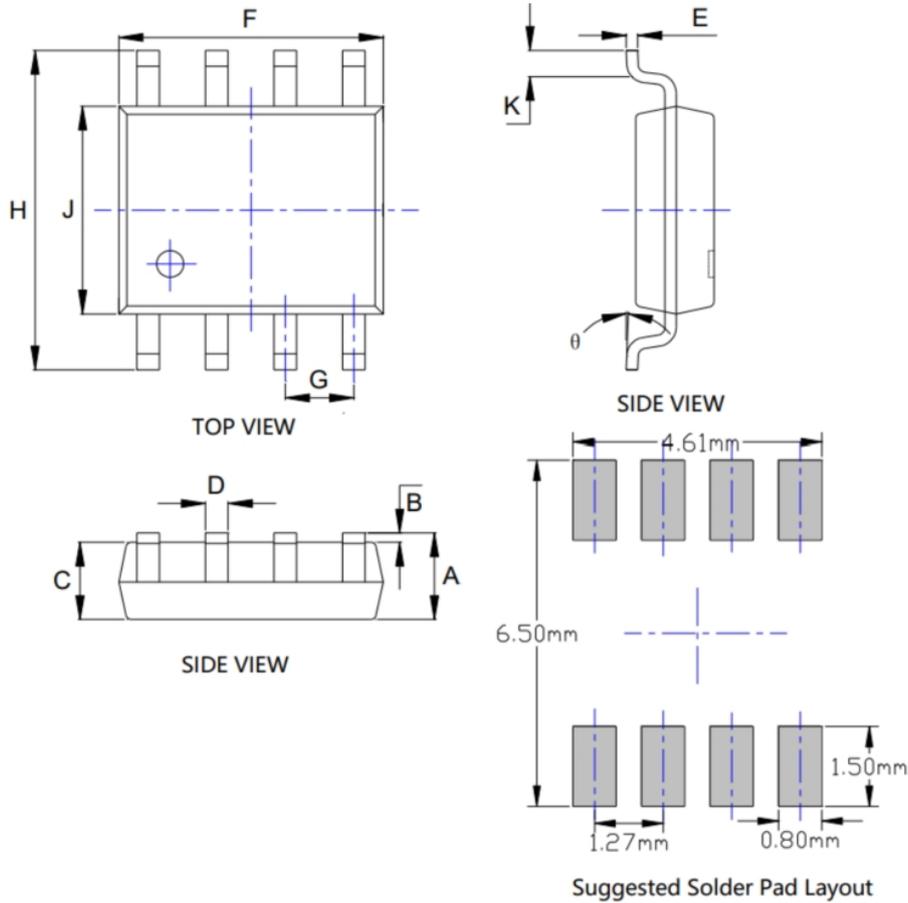
SOP-8L(X) Package Information



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.10	0.15	0.25
A2	1.25	1.40	1.65
A3	0.50	0.60	0.70
b	0.38	—	0.51
b1	0.37	0.42	0.47
c	0.18	—	0.25
c1	0.17	0.20	0.23
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e	1.17	1.27	1.37
L	0.45	0.60	0.80
L1	1.04REF		
L2	0.25BSC		
R	0.07	—	—
R1	0.07	—	—
h	0.30	0.40	0.50
θ	0°	—	8°
θ 1	15°	17°	19°
θ 2	11°	13°	15°
θ 3	15°	17°	19°
θ 4	11°	13°	15°

SOP-8L(R) Package Information



DIMENSIONS				
SYMBOL	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.053	0.069	1.350	1.750
B	0.004	0.010	0.100	0.250
C	0.053	0.061	1.350	1.550
D	0.013	0.020	0.330	0.510
E	0.007	0.010	0.170	0.250
F	0.189	0.197	4.800	5.000
G	0.050BSC		1.270BSC	
H	0.228	0.244	5.800	6.200
J	0.150	0.157	3.800	4.000
K	0.016	0.050	0.400	1.270
$\theta$	0°	8°	0°	8°

Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.

### Revision History

Revision	Date	Subjects
V2.0	2025.12	Update some parameters and curves.

### Attention

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